

Product Summary

| BV _{DSS} | R _{DS(ON)} Max | I _D Max T _A = +25°C |
|-------------------|----------------------------|--|
| 60V | 2Ω @ V _{GS} = 10V | 550mA |
| | 3Ω @ V _{GS} = 5V | |

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Power Management Functions
- Backlighting

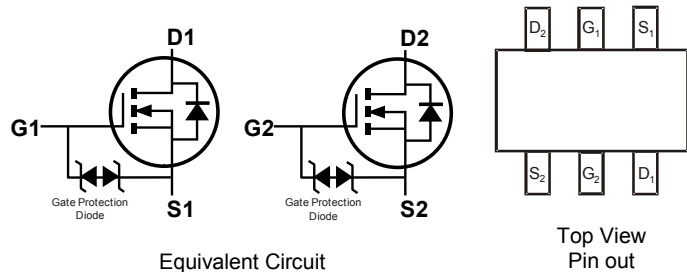
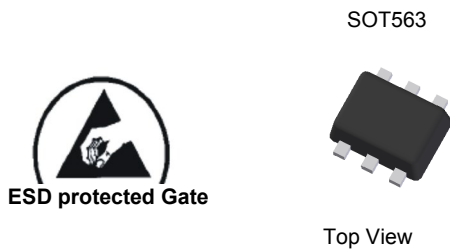
Features and Benefits

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected up to 2kV
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.006 grams (Approximate)

NEW PRODUCT

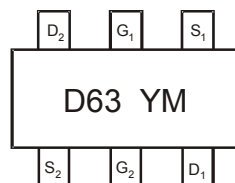


Ordering Information (Note 4)

| Part Number | Case | Packaging |
|--------------|--------|-------------------|
| DMN63D1LV-7 | SOT563 | 3000/Tape & Reel |
| DMN63D1LV-13 | SOT563 | 10000/Tape & Reel |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



D63 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: C = 2015)
 M = Month (ex: 9 = September)

Date Code Key

| Year | 2014 | 2015 | 2016 | 2017 | 2018 | 2019 | 2020 | 2021 | 2022 | 2023 | 2024 | 2025 |
|------|------|------|------|------|------|------|------|------|------|------|------|------|
| Code | B | C | D | E | F | G | H | I | J | K | L | M |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | O | N | D |

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | |
|--|--------------|---------------------------|------|----|
| Drain-Source Voltage | V_{DSS} | 60 | V | |
| Gate-Source Voltage | V_{GSS} | ± 20 | V | |
| Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$ | Steady State | $T_A = +25^\circ\text{C}$ | 550 | mA |
| | | $T_A = +70^\circ\text{C}$ | 450 | |
| Maximum Continuous Body Diode Forward Current (Note 6) | I_S | 0.5 | A | |
| Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%) | I_{DM} | 1.2 | A | |

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |
|--|------------------------------|-------------|--------------------|
| Total Power Dissipation (Note 5) | P_D | 450 | mW |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State $R_{\theta JA}$ | 283 | $^\circ\text{C/W}$ |
| Total Power Dissipation (Note 6) | P_D | 940 | mW |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State $R_{\theta JA}$ | 133 | $^\circ\text{C/W}$ |
| Operating and Storage Temperature Range | T_J, T_{STG} | -55 to +150 | $^\circ\text{C}$ |

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|---|--------------|-----|------|----------|---------------|---|
| OFF CHARACTERISTICS (Note 7) | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | 60 | — | — | V | $V_{GS} = 0\text{V}, I_D = 10\mu\text{A}$ |
| Zero Gate Voltage Drain Current | I_{DSS} | — | — | 1.0 | μA | $V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$ |
| Gate-Source Leakage | I_{GSS} | — | — | ± 10 | μA | $V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$ |
| ON CHARACTERISTICS (Note 7) | | | | | | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | 1.0 | 1.6 | 2.5 | V | $V_{DS} = 10\text{V}, I_D = 1\text{mA}$ |
| Static Drain-Source On-Resistance | $R_{DS(ON)}$ | — | — | 2.0 | Ω | $V_{GS} = 10\text{V}, I_D = 0.5\text{A}$ |
| | | — | — | 3.0 | | $V_{GS} = 5\text{V}, I_D = 0.05\text{A}$ |
| Forward Transfer Admittance | $ Y_{fs} $ | 80 | — | — | mS | $V_{DS} = 10\text{V}, I_D = 0.2\text{A}$ |
| Diode Forward Voltage | V_{SD} | — | 0.75 | 1.2 | V | $V_{GS} = 0\text{V}, I_S = 115\text{mA}$ |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | | |
| Input Capacitance | C_{iss} | — | 30 | — | pF | $V_{DS} = 25\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$ |
| Output Capacitance | C_{oss} | — | 4.2 | — | pF | |
| Reverse Transfer Capacitance | C_{rss} | — | 2.9 | — | pF | |
| Gate Resistance | R_g | — | 133 | — | Ω | $f = 1\text{MHz}, V_{GS} = 0\text{V}, V_{DS} = 0\text{V}$ |
| Total Gate Charge | Q_g | — | 392 | — | pC | $V_{GS} = 4.5\text{V}, V_{DS} = 10\text{V},$ $I_D = 250\text{mA}$ |
| Gate-Source Charge | Q_{gs} | — | 157 | — | pC | |
| Gate-Drain Charge | Q_{gd} | — | 92 | — | pC | |
| Turn-On Delay Time | $t_{D(ON)}$ | — | 3.9 | — | ns | $V_{DD} = 30\text{V}, V_{GS} = 10\text{V},$ $R_G = 25\Omega, I_D = 200\text{mA}$ |
| Turn-On Rise Time | t_R | — | 3.4 | — | ns | |
| Turn-Off Delay Time | $t_{D(OFF)}$ | — | 15.7 | — | ns | |
| Turn-Off Fall Time | t_F | — | 9.9 | — | ns | |

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 - Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

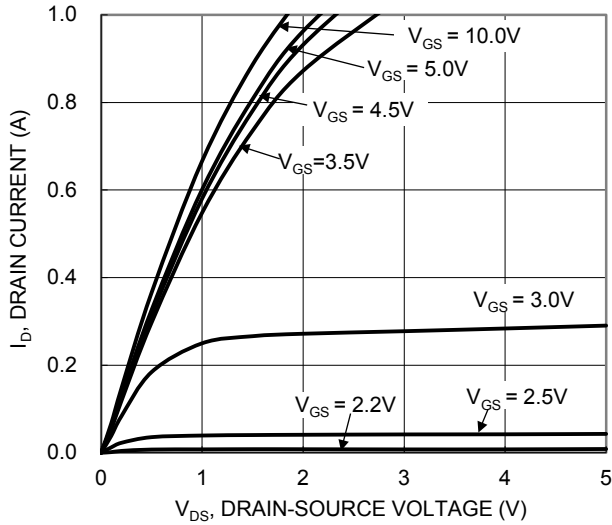


Figure 1. Typical Output Characteristic

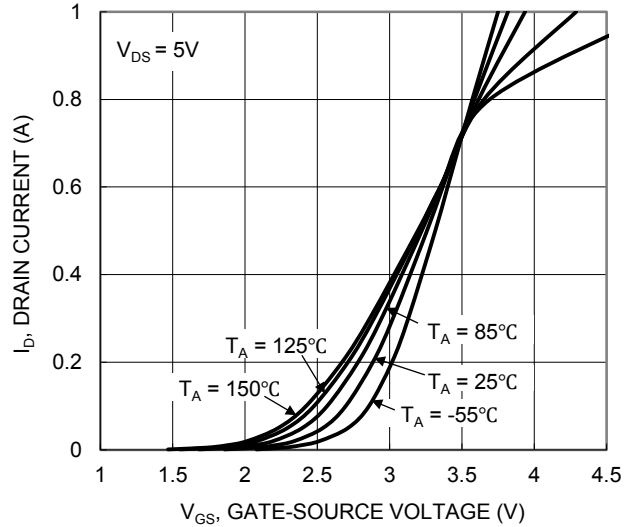


Figure 2. Typical Transfer Characteristic

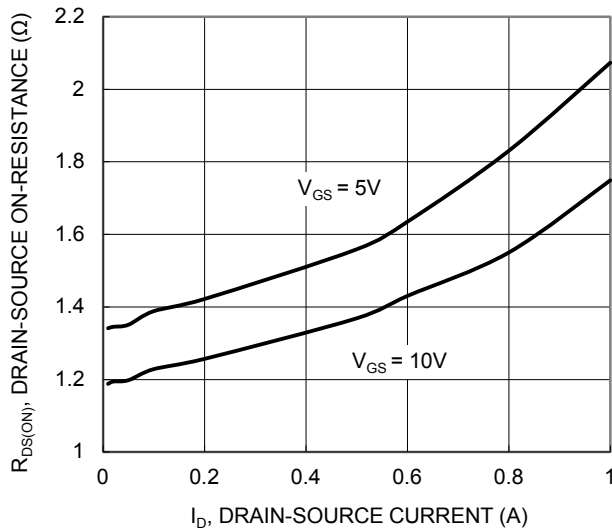


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

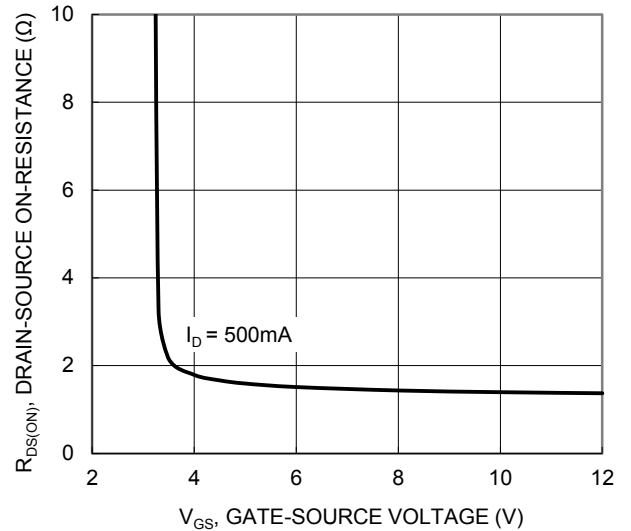


Figure 4. Typical Transfer Characteristic

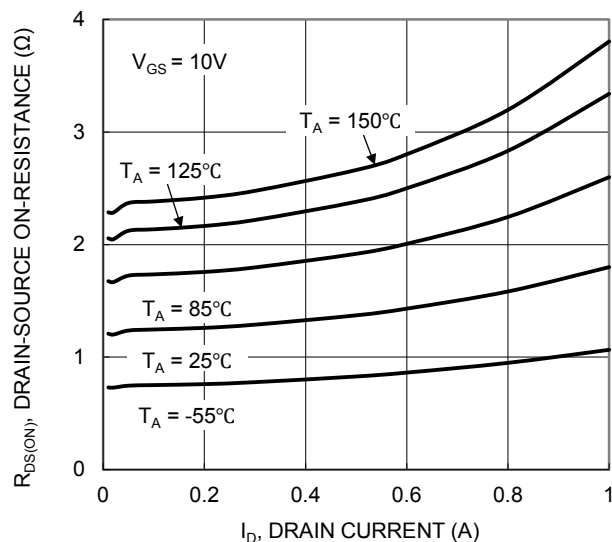


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

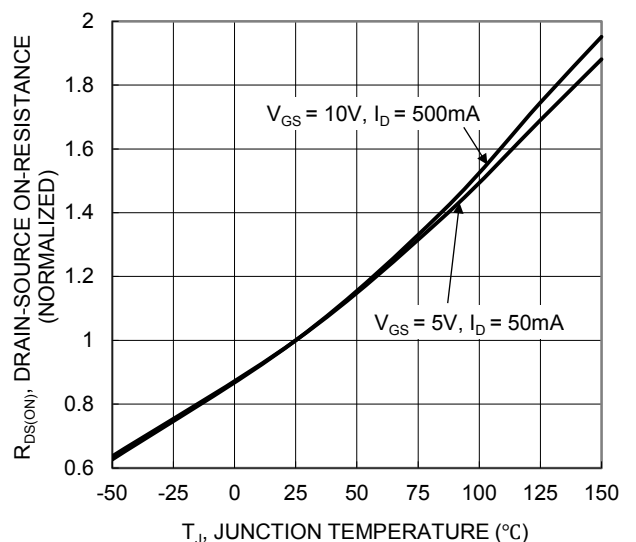


Figure 6. On-Resistance Variation with Junction Temperature

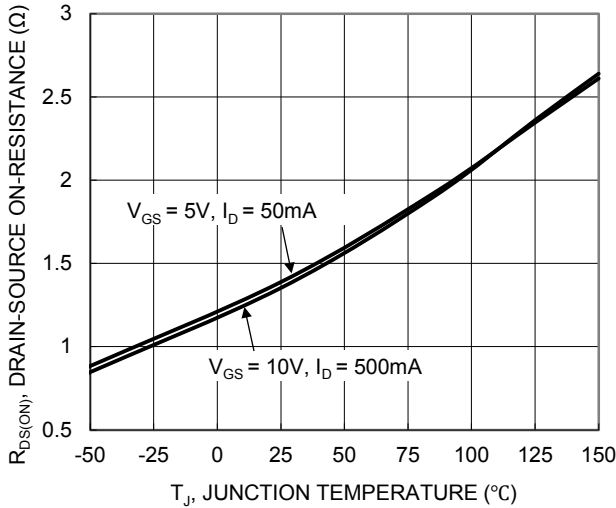


Figure 7. On-Resistance Variation with Junction Temperature

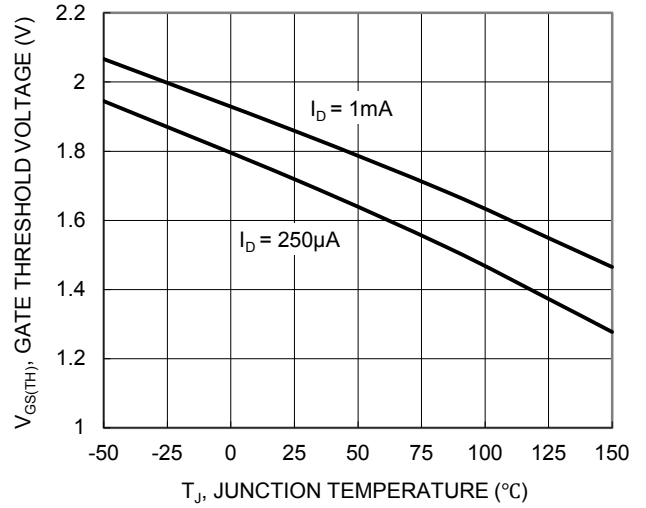


Figure 8. Gate Threshold Variation vs. Junction Temperature

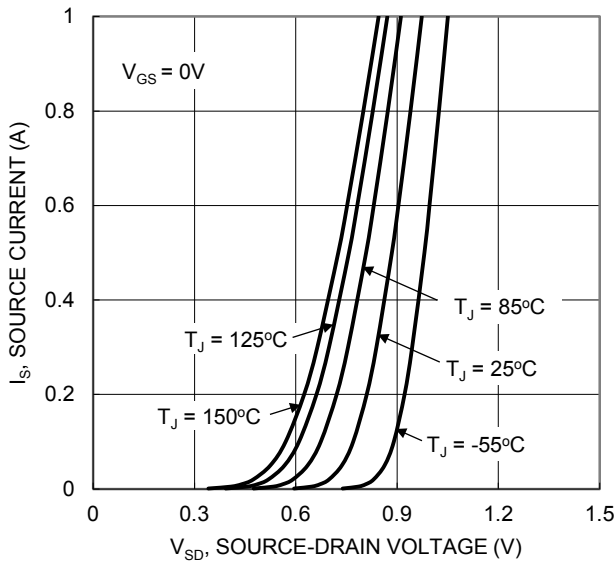


Figure 9. Diode Forward Voltage vs. Current

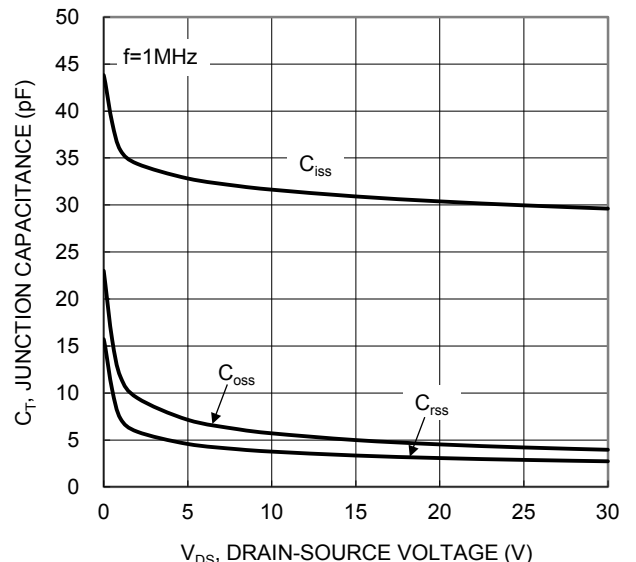


Figure 10. Typical Junction Capacitance

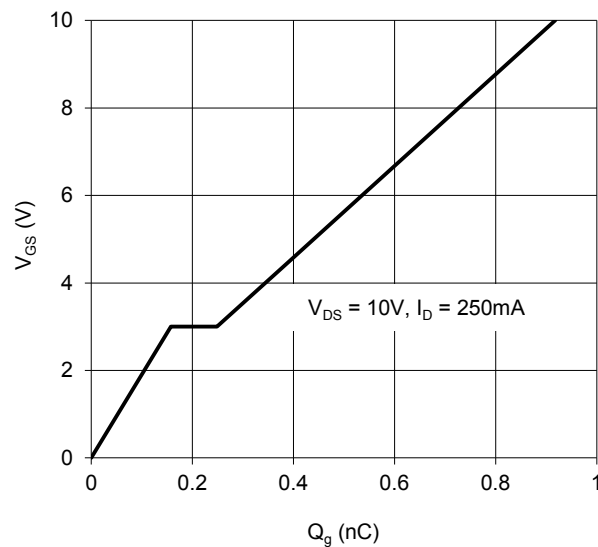


Figure 11. Gate Charge

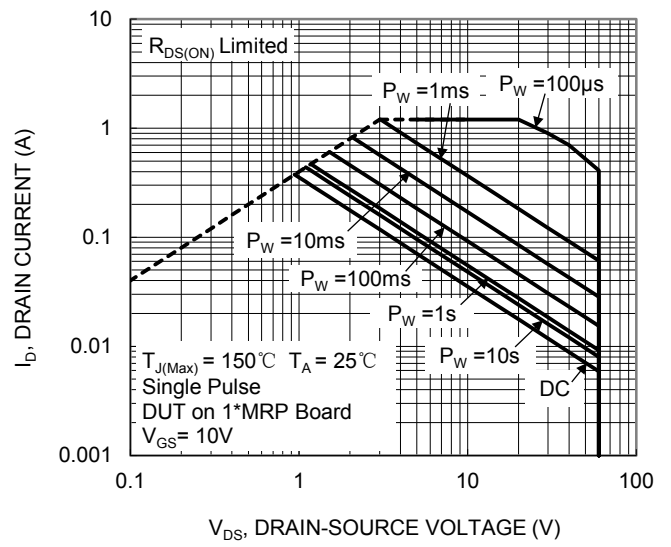


Figure 12. SOA, Safe Operation Area

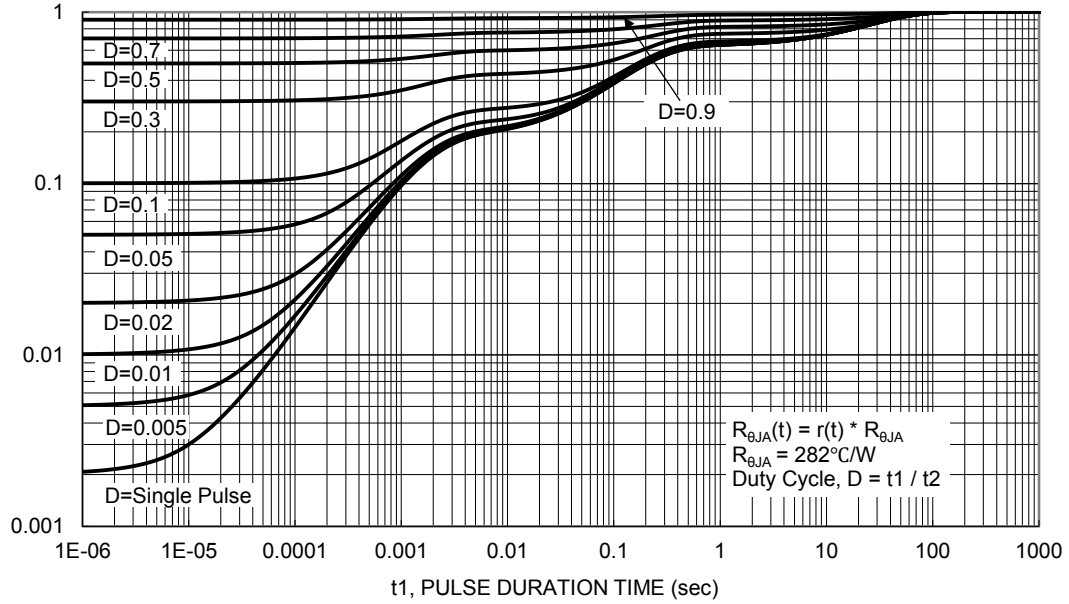
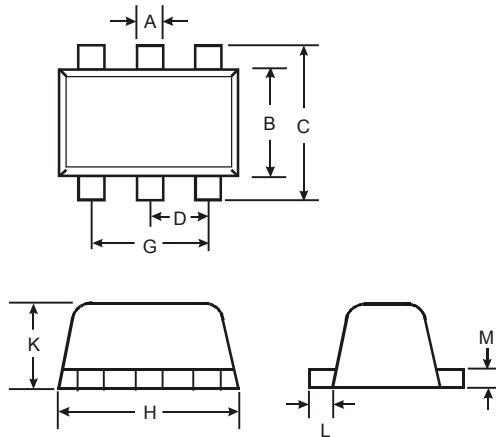


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

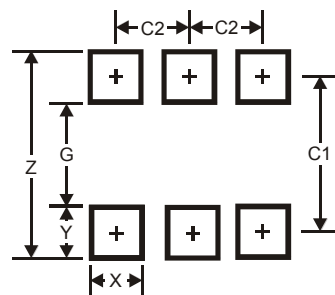
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



| SOT563 | | | |
|----------------------|------|------|------|
| Dim | Min | Max | Typ |
| A | 0.15 | 0.30 | 0.20 |
| B | 1.10 | 1.25 | 1.20 |
| C | 1.55 | 1.70 | 1.60 |
| D | - | - | 0.50 |
| G | 0.90 | 1.10 | 1.00 |
| H | 1.50 | 1.70 | 1.60 |
| K | 0.55 | 0.60 | 0.60 |
| L | 0.10 | 0.30 | 0.20 |
| M | 0.10 | 0.18 | 0.11 |
| All Dimensions in mm | | | |

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| Z | 2.2 |
| G | 1.2 |
| X | 0.375 |
| Y | 0.5 |
| C1 | 1.7 |
| C2 | 0.5 |

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